

CORRECTION

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Correction: Charge transfer doping with an organic layer to achieve a high-performance p-type WSe₂ transistorMinho Yoon^a and Jiyoul Lee^{*ab}

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Correction for 'Charge transfer doping with an organic layer to achieve a high-performance p-type WSe₂ transistor' by Minho Yoon *et al.*, *J. Mater. Chem. C*, 2021, DOI: 10.1039/D1TC01780B.

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The authors regret an error in Fig. 1 of the published article, where Fig. 1(d) was replaced with a copy of Fig. 1(c). The corrected form of Fig. 1 is shown below:

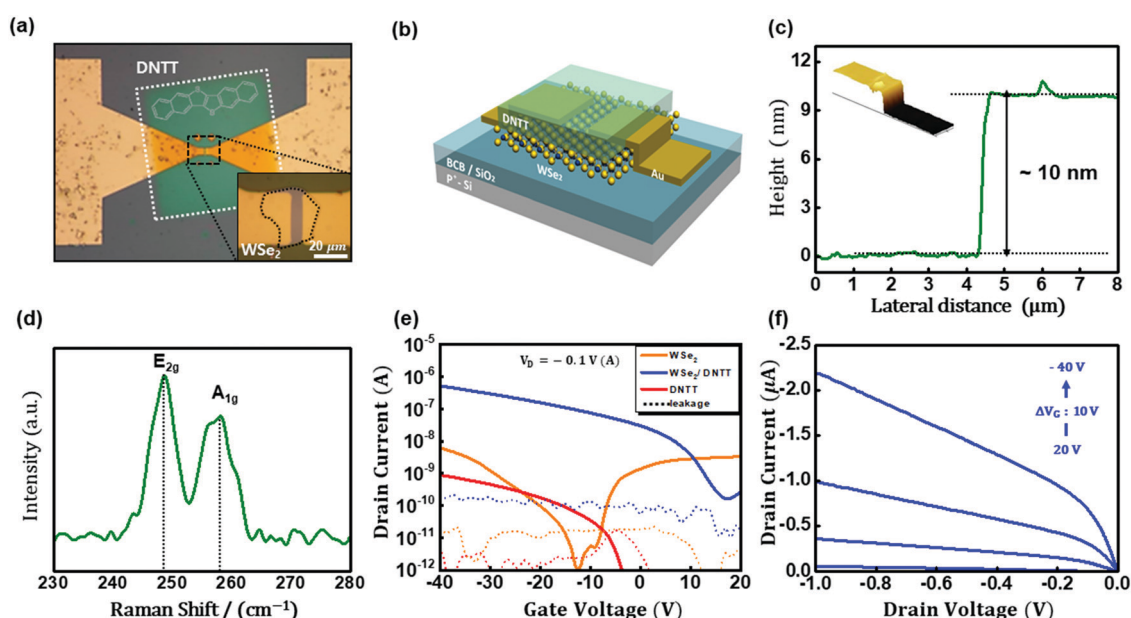


Fig. 1 (a) Optical micrograph of the WSe₂/dinaphtho[2,3-*b*:2',3'-*f*]thieno[3,2-*b*]thiophene (DNNT) field-effect transistor (FET), along with Au source (S)/drain (D) electrodes; the green square region is patterned DNNT, and the inset shows a magnified S/D region over the WSe₂ FET channel. (b) Three-dimensional schematics of the WSe₂/DNNT FET on a hydrophobic benzocyclobutene (BCB) (300 nm)/SiO₂ (285 nm) dielectric support. (c) Atomic force microscopy image and thickness profile (~10 nm) of the WSe₂ FET channel. (d) Raman spectrum of the WSe₂ flake, before DNNT deposition; the peaks near 250 and 257 cm⁻¹ correspond to the in-plane (E_{2g}) and out-of-plane (A_{1g}) vibrational modes, respectively. (e) Transfer characteristics of DNNT and the WSe₂ FET before and after DNNT deposition. (f) Output characteristics of the WSe₂/DNNT FET.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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